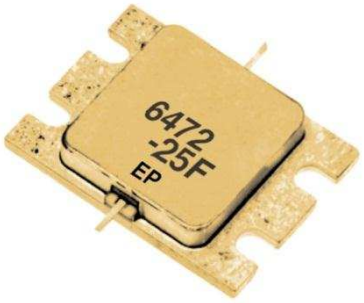
FLM6472-25F

C-Band Internally Matched FET



FEATURES

- High Output Power: P_{1dB} = 44.5dBm (Typ.)
- High Gain: G_{1dB} = 9.5dB (Typ.)
- High PAE: η_{add} = 38% (Typ.)
- Low IM3 = -46dBc@Po = 33.5dBm
- Broad Band: 6.4 to 7.2GHz
- Impedance Matched Zin/Zout = 50ohm
- Hermetically Sealed Package

DESCRIPTION

The FLM6472-25F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.
SEDI's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Case Temperature Tc=25deg.C)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	T_c = 25deg.C	93.7	W
Storage Temperature	T_{stg}		-65 to +175	deg.C
Channel Temperature	T_{ch}		175	deg.C

SEDI recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 64.0 and -11.2 mA respectively with gate resistance of 25ohm.

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25deg.C)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	V_{DS}=5V, V_{GS}=0V	-	10	15	A
Transconductance	g_m	V_{DS}=5V, I_{DS}=6500mA	-	10	-	S
Pinch-off Voltage	V_p	V_{DS}=5V, I_{DS}=500mA	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	I_{GS}=-500uA	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	V_{DS}=10V, I_{DS}=0.65 I_{DSS} (Typ.), f=6.4 to 7.2 GHz, Z_S=Z_L=50ohm	43.5	44.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		8.5	9.5	-	dB
Drain Current	I_{dsr}		-	6500	7600	mA
Power-added Efficiency	η_{add}		-	38	-	%
Gain Flatness	ΔG		-	-	1.2	dB
3rd Order Intermodulation Distortion	IM_3	f = 7.2 GHz, Δf = 10 MHz 2-Tone Test Pout = 33.5dBm S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	1.4	1.6	deg.C/W
Channel Temperature Rise	ΔT_{ch}	10V x I_{dsr} x R_{th}	-	-	80	deg.C

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

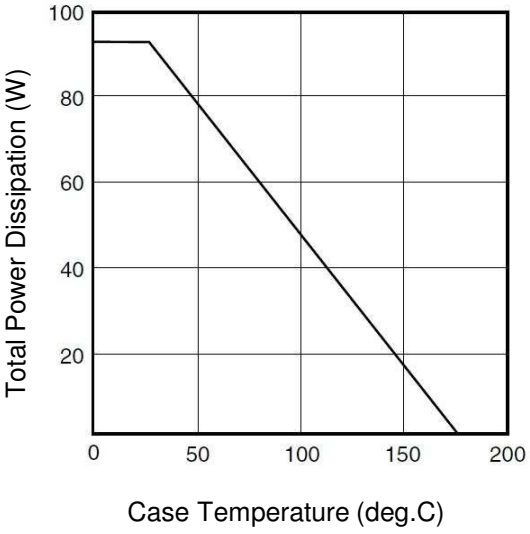
CASE STYLE	IK

ESD	Class 3A	4000V to 8000V

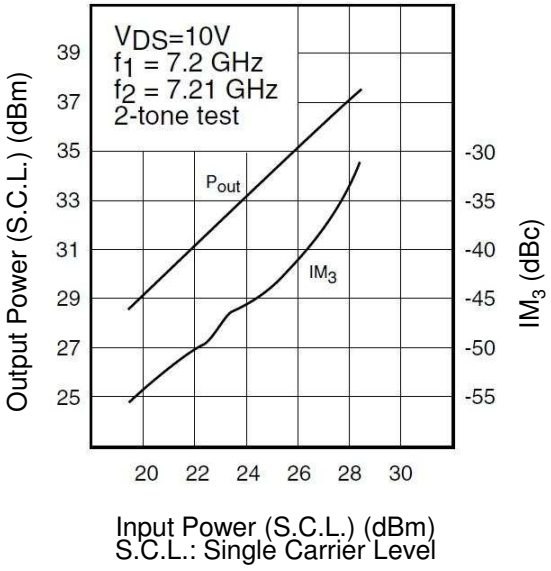
Note : Based on JEDEC JESD22-A114 (C=100pF, R=1.5kohm)

RoHS Compliance	Yes

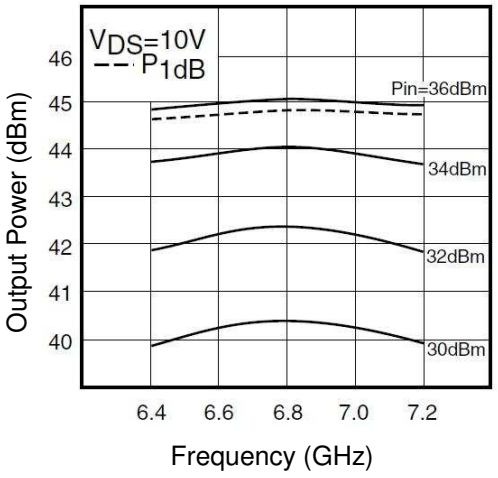
POWER DERATING CURVE



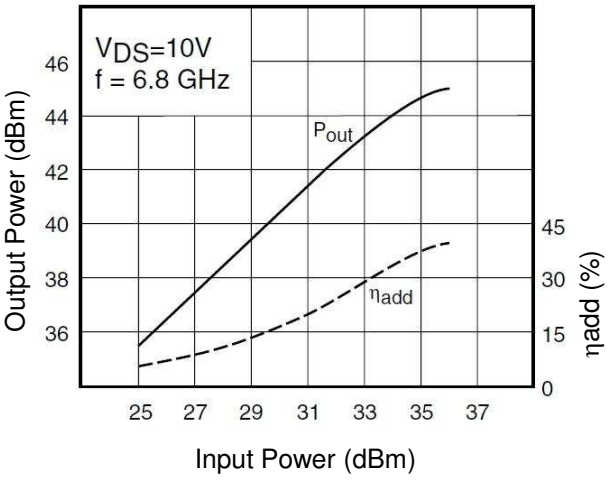
OUTPUT POWER & IM_3 vs. INPUT POWER

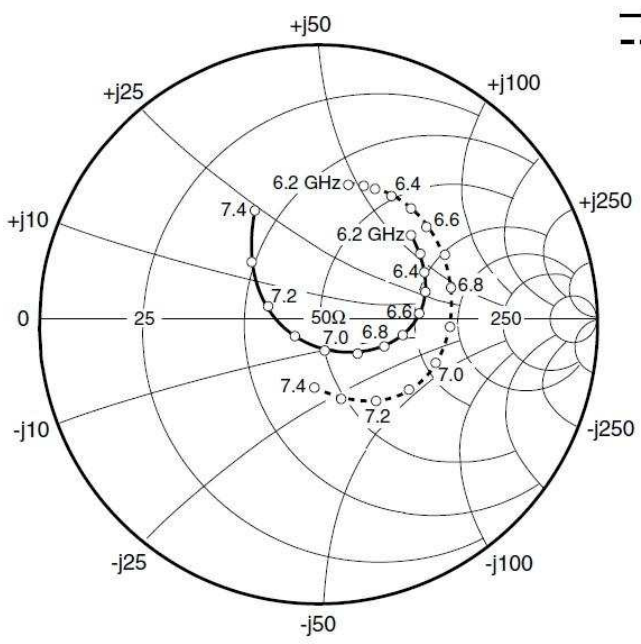


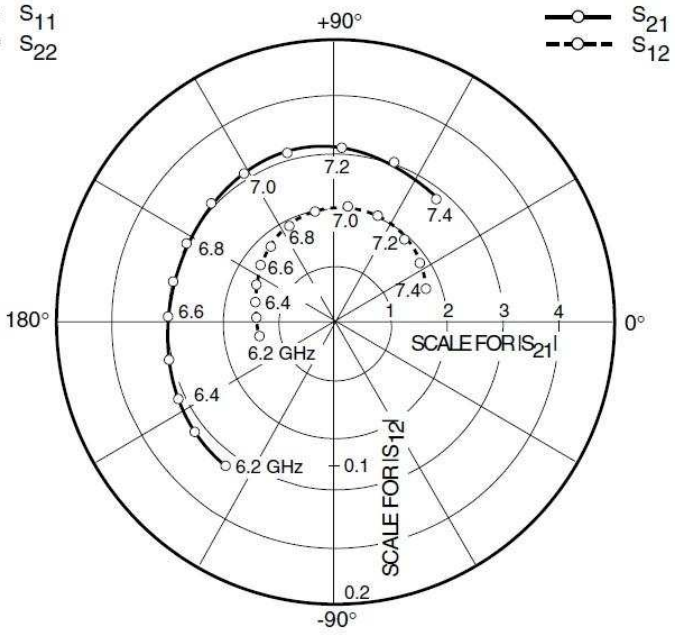
OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





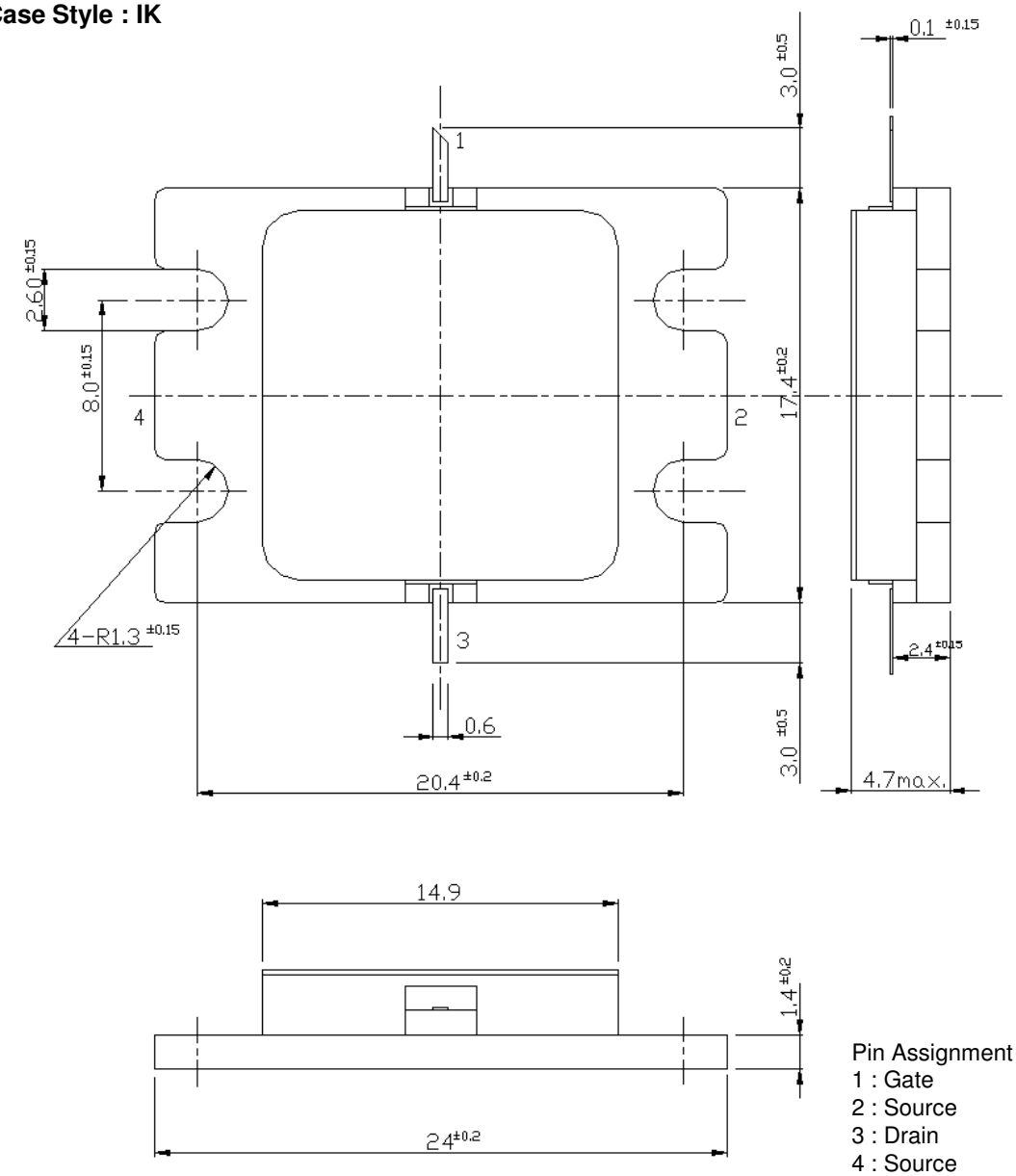


S-PARAMETERS

V_{DS} = 10V, I_{DS} = 6500mA

FREQUENCY	S11		S21		S12		S22	
(MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6200	0.456	42.1	3.198	-129.2	0.057	-169.6	0.510	71.7
6300	0.444	33.6	3.139	-143.1	0.058	179.0	0.512	66.4
6400	0.426	24.4	3.089	-154.7	0.061	167.8	0.512	59.8
6500	0.397	15.3	3.018	-167.8	0.064	156.1	0.513	51.4
6600	0.358	4.4	3.044	178.4	0.069	144.0	0.512	41.3
6700	0.312	-6.6	3.038	165.6	0.071	131.3	0.502	28.9
6800	0.254	-21.0	3.063	151.7	0.076	117.2	0.488	14.6
6900	0.183	-40.2	3.101	136.9	0.079	101.6	0.466	-1.8
7000	0.114	-77.1	3.148	121.1	0.081	84.6	0.437	-19.7
7100	0.104	-149.7	3.164	105.9	0.082	68.7	0.401	-37.0
7200	0.195	164.3	3.139	88.1	0.076	53.1	0.354	-55.3
7300	0.325	138.9	3.042	69.6	0.073	32.7	0.298	-74.2
7400	0.454	120.5	2.871	50.6	0.069	19.4	0.238	-93.9

■ **Package Outline**
Case Style : IK



Pin Assignment
1 : Gate
2 : Source
3 : Drain
4 : Source

Unit : mm

For further information please contact:

http://global-sei.com/Electro-optic/about/office.html

CAUTION

This product contains **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

・Do not put these products into the mouth.

・Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.

・Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.